

Maria N Koryazhkina

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5366338/publications.pdf>

Version: 2024-02-01

23
papers

394
citations

933447

10
h-index

752698

20
g-index

23
all docs

23
docs citations

23
times ranked

249
citing authors

#	ARTICLE	IF	CITATIONS
1	Silicon-Compatible Memristive Devices Tailored by Laser and Thermal Treatments. Journal of Low Power Electronics and Applications, 2022, 12, 14.	2.0	3
2	Stochastic resonance in a metal-oxide memristive device. Chaos, Solitons and Fractals, 2021, 144, 110723.	5.1	101
3	A neurohybrid memristive system for adaptive stimulation of hippocampus. Chaos, Solitons and Fractals, 2021, 146, 110804.	5.1	15
4	Stochastic model of memristor based on the length of conductive region. Chaos, Solitons and Fractals, 2021, 150, 111131.	5.1	16
5	Multilayer Metal-Oxide Memristive Device with Stabilized Resistive Switching. Advanced Materials Technologies, 2020, 5, 1900607.	5.8	78
6	Experimental investigations of local stochastic resistive switching in yttria stabilized zirconia film on a conductive substrate. Journal of Statistical Mechanics: Theory and Experiment, 2020, 2020, 024005.	2.3	3
7	Mechanisms of Current Transport and Resistive Switching in Capacitors with Yttria-Stabilized Hafnia Layers. Technical Physics, 2019, 64, 873-880.	0.7	4
8	The Effect of Irradiation with Si ⁺ Ions on Resistive Switching in Memristive Structures Based on Yttria-Stabilized Zirconia. Technical Physics Letters, 2019, 45, 690-693.	0.7	2
9	Study of Local Charge Accumulation in ZrO ₂ (Y) Films with Au Nanoparticles by Kelvin Probe Force Microscopy. Journal of Surface Investigation, 2019, 13, 30-35.	0.5	0
10	Noise-induced resistive switching in a memristor based on ZrO ₂ (Y)/Ta ₂ O ₅ stack. Journal of Statistical Mechanics: Theory and Experiment, 2019, 2019, 124026.	2.3	82
11	Atomic-Force Microscopy of Resistive Nonstationary Signal Switching in ZrO ₂ (Y) Films. Technical Physics, 2019, 64, 1579-1583.	0.7	2
12	Investigation of local charge accumulation in yttria stabilized zirconia films with Au nanoparticles by Scanning Kelvin Probe Microscopy. Journal of Physics: Conference Series, 2018, 1124, 081028.	0.4	0
13	Bipolar resistive switching in metal-insulator-semiconductor nanostructures based on silicon nitride and silicon oxide. Journal of Physics: Conference Series, 2018, 993, 012028.	0.4	7
14	Ion Migration Polarization in the Yttria Stabilized Zirconia Based Metal-Oxide-Metal and Metal-Oxide-Semiconductor Stacks for Resistive Memory. Advances in Condensed Matter Physics, 2018, 2018, 1-8.	1.1	12
15	Fabrication of Metal Nanoparticle Arrays in the ZrO ₂ (Y), HfO ₂ (Y), and GeO _x Films by Magnetron Sputtering. Advances in Materials Science and Engineering, 2017, 2017, 1-7.	1.8	7
16	Resistive switching in the Au/Zr/ZrO ₂ -Y ₂ O ₃ /TiN/Ti memristive devices deposited by magnetron sputtering. Journal of Physics: Conference Series, 2016, 741, 012174.	0.4	11
17	Electrical and photoelectric properties of Si-based metal-insulator-semiconductor structures with Au nanoparticles at the insulator-semiconductor interface. Semiconductors, 2016, 50, 1614-1618.	0.5	1
18	Physical properties of metal-insulator-semiconductor structures based on n-GaAs with InAs quantum dots deposited onto the surface of an n-GaAs layer. Semiconductors, 2016, 50, 1589-1594.	0.5	1

#	ARTICLE	IF	CITATIONS
19	Specific features of nonequilibrium depletion accompanied by the trapping of minority carriers by surface states in metal-insulator-semiconductor structures. Technical Physics Letters, 2016, 42, 138-142.	0.7	3
20	Light-induced resistive switching in silicon-based metal-insulator-semiconductor structures. Technical Physics Letters, 2016, 42, 536-538.	0.7	18
21	The forming process in resistive-memory elements based on metal-insulator-semiconductor structures. Technical Physics Letters, 2014, 40, 837-840.	0.7	10
22	Capacitors with nonlinear characteristics based on stabilized zirconia with built-in gold nanoparticles. Technical Physics Letters, 2014, 40, 369-371.	0.7	13
23	Features of Fermi-level pinning at the interface of Al _{0.3} Ga _{0.7} As with anodic oxide and stabilized zirconia. Technical Physics Letters, 2013, 39, 1064-1067.	0.7	5